

FQA6N80 Information



For Reference Only

Part Number FQA6N80

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 6.3A TO-3P

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQA6N80 Specifications

Manufacturer Part Number FQA6N80 Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 6.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 3InC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1500pF @ 25V Vgs (Max) 250V FET Feature - Power Dissipation (Max) 185W (Tc) Rds On (Max) @ Id, Vgs 1.95 Ohm @ 3.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P-3, SC-65-3 Package / Case TO-3P-3, SC-65-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C6.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs31nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1500pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)185W (Tc)Rds On (Max) @ Id, Vgs1.95 Ohm @ 3.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Package	TO-3P-3, SC-65-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C6.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs31nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1500pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)185W (Tc)Rds On (Max) @ Id, Vgs1.95 Ohm @ 3.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Series	QFET?
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Current - Continuous Drain (Id) @ 25°C6.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs31nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1500pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)185W (Tc)Rds On (Max) @ Id, Vgs1.95 Ohm @ 3.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Technology	MOSFET (Metal Oxide)
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Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Iso0pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.95 Ohm @ 3.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Current - Continuous Drain (Id) @ 25°C	6.3A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1500pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.95 Ohm @ 3.15A, 10V Operating Temperature Jensel Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1500pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.95 Ohm @ 3.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)185W (Tc)Rds On (Max) @ Id, Vgs1.95 Ohm @ 3.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Gate Charge (Qg) (Max) @ Vgs	31nC @ 10V
FET Feature - Rower Dissipation (Max) 185W (Tc) Rds On (Max) @ Id, Vgs 1.95 Ohm @ 3.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Input Capacitance (Ciss) (Max) @ Vds	1500pF @ 25V
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Rds On (Max) @ Id, Vgs 1.95 Ohm @ 3.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Power Dissipation (Max)	185W (Tc)
Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Rds On (Max) @ Id, Vgs	1.95 Ohm @ 3.15A, 10V
Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-3P-3, SC-65-3	Mounting Type	Through Hole
	Supplier Device Package	TO-3P
Report errors?	Package / Case	TO-3P-3, SC-65-3
		Report errors?

FQA6N80 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQA6N80 Payment Methods



















FQA6N80 Shipping Methods













If you have any question about FQA6N80, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com